

ABSTRACT OF THE DISCLOSURE

According to one aspect of the invention, a method of constructing a memory array is provided. An insulating layer is formed on a semiconductor wafer. A first metal stack is then formed on the insulating layer and etched to form first metal lines. A polymeric layer is formed over the first metal lines and the insulating layer. A puddle of smoothing solvent is then allowed to stand on the wafer. The smoothing solvent is then removed. After the smoothing solvent is removed, the polymeric layer has a reduced surface roughness. A second metal stack is then formed on the polymeric layer and etched to form second metal lines.